

ABSTRACT OF THE DISCLOSURE

A substrate treating method and apparatus are disclosed, which are capable of treating substrates having a material of high dielectric constant, reliably at a relatively
5 low temperature. A treating solution containing sulfuric acid (H_2SO_4) and hydrofluoric acid (HF) or sulfuric acid (H_2SO_4) and buffered hydrofluoric acid ($\text{NH}_4\text{F} \cdot \text{HF}$) is used for treating substrates coated with a film including the material of high dielectric constant. The material of high
10 dielectric constant may be treated selectively by the treating solution at the relatively low temperature.